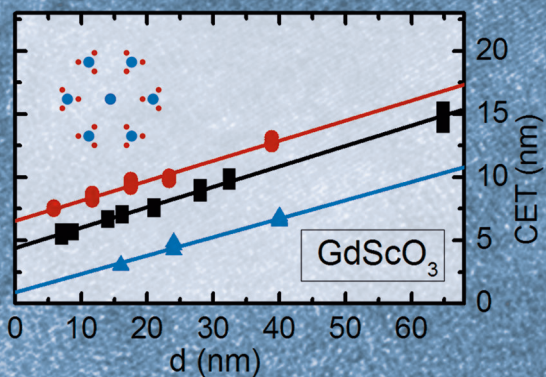
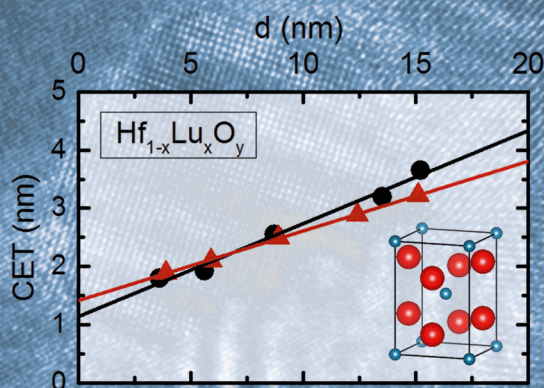


Growth and characterization of crystalline rare-earth based thin oxide films for the application as gate dielectric in nanotechnology

Anna Barbara Schäfer



Forschungszentrum Jülich GmbH
Peter Grünberg Institute
Semiconductor Nanoelectronics (PGI-9)

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